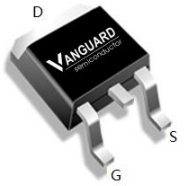
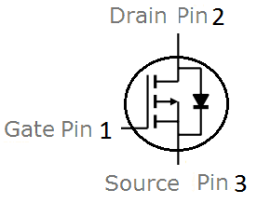
Features

- P-Channel，-5V Logic Level Control
- Low on-resistance RDS(on) @ V_{GS}=-4.5 V
- Fast Switching and High efficiency
- Enhancement mode
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant

V_{DS}	-100	V
$R_{DS(on),TYP}$@ V_{GS}=-10 V	47	mΩ
$R_{DS(on),TYP}$@ V_{GS}=-4.5V	49	mΩ
I_D	-34	A

TO-252





Pb-Free RoHS Halogen-Free

Part ID	Package Type	Marking	Tape and reel information
VSD050P10MS	TO-252	050P10M	2500PCS/Reel

Maximum ratings, at T_A=25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		-100	V
V_{GS}	Gate-Source voltage		±20	V
I_S	Diode continuous forward current	T_C=25°C	-34	A
I_D	Continuous drain current @V_{GS}=-10V	T_C=25°C	-34	A
		T_C=100°C	-24	A
I_{DM}	Pulse drain current tested ①	T_C=25°C	-136	A
I_{DSM}	Continuous drain current @VGS=-10V	T_A=25°C	-3.8	A
		T_A=70°C	-3	A
EAS	Avalanche energy, single pulsed ②		163	mJ
P_D	Maximum power dissipation	T_C=25°C	100	W
P_{DSM}	Maximum power dissipation ③	T_A=25°C	1.3	W
T_{STG}, T_J	Storage and Junction Temperature Range		-55 to 175	°C
Thermal Characteristics				
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		100	°C/W

Typical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-100	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-100V,V_{GS}=0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(Tj=125℃)	V_{DS}=-100V,V_{GS}=0V	--	--	-100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=-250μA	-1.3	-1.6	-2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance ④	V_{GS}=-10V, I_D=-20A	--	47	61	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance ④	V_{GS}=-4.5V, I_D=-10A	--	49	62	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=-30V,V_{GS}=0V, f=1MHz	4345	5110	5875	pF
C_{oss}	Output Capacitance		155	180	205	pF
C_{rss}	Reverse Transfer Capacitance		120	140	160	pF
Q_g (10V)	Total Gate Charge	V_{DS}=-50V,I_D=-20A, V_{GS}=-10V	--	85	--	nC
Q_g (4.5V)	Total Gate Charge		--	49	--	nC
Q_{gs}	Gate-Source Charge		--	17	--	nC
Q_{gd}	Gate-Drain Charge		--	20	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=-50V, I_D=-20A, R_G=3.0Ω, V_{GS}=-10V	--	19.5	--	ns
t_r	Turn-on Rise Time		--	22	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	85.5	--	ns
t_f	Turn-Off Fall Time		--	39	--	ns
Source- Drain Diode Characteristics@ T_J = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=-20A,V_{GS}=0V	--	-0.9	-1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=-20A, V_{GS}=0V di/dt=-500A/μs	--	29	--	ns
Q_{rr}	Reverse Recovery Charge		--	167	--	nC

NOTE:

① Repetitive rating; pulse width limited by max junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH, R_G = 25Ω, I_{AS} =-20A, V_{GS} =-10V. Part not recommended for use above this value

③ The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.

④ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

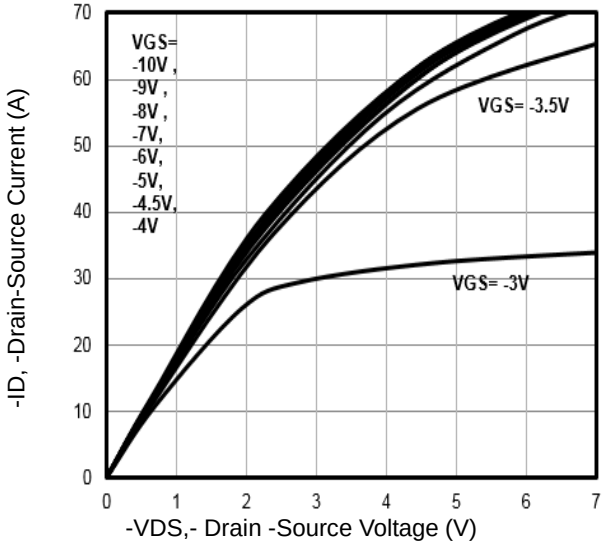


Fig1. Typical Output Characteristics

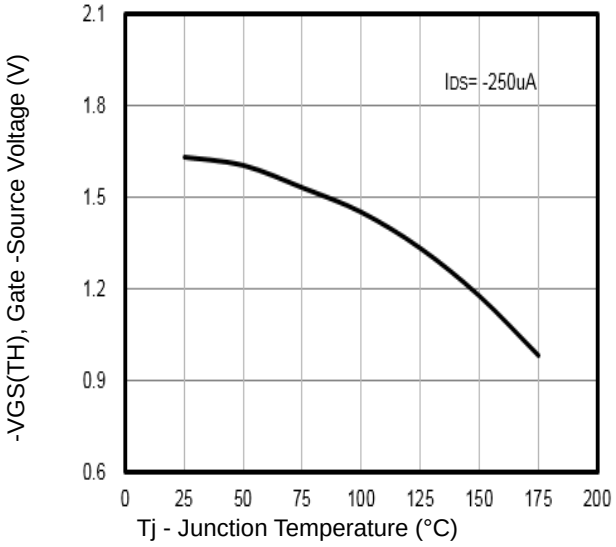


Fig2. $-V_{GS(TH)}$ Gate -Source Voltage Vs.Tj

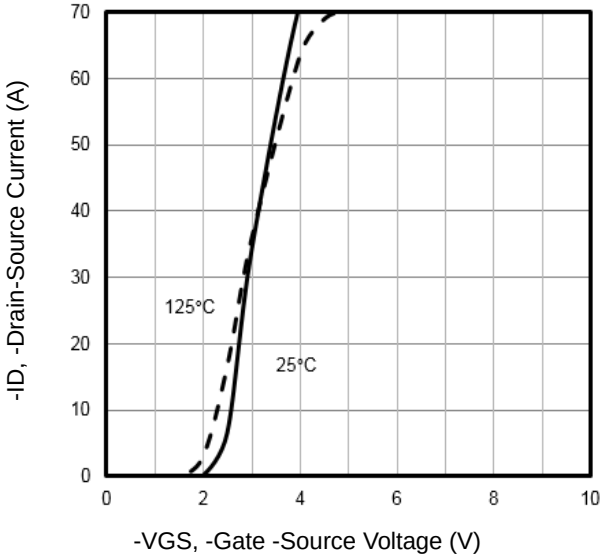


Fig3. Typical Transfer Characteristics

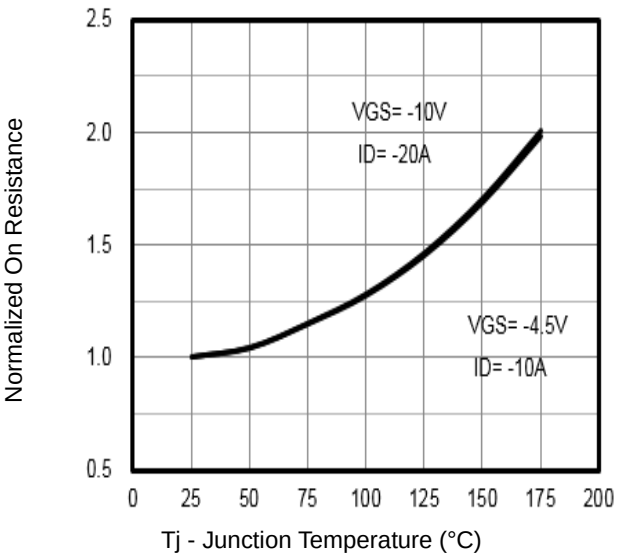


Fig4. Normalized On-Resistance Vs. Tj

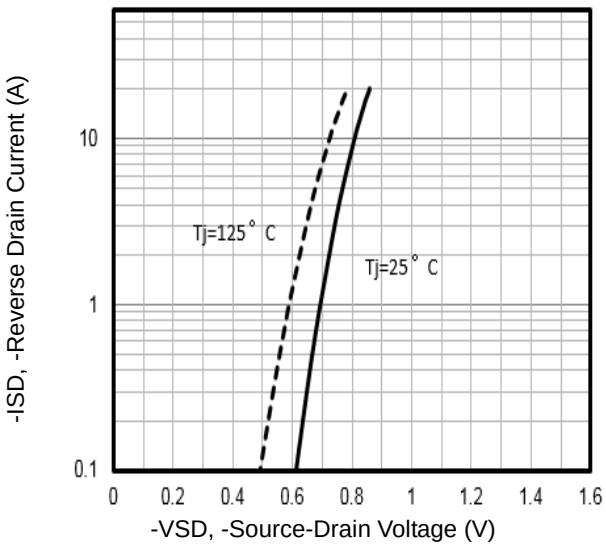


Fig5. Typical Source-Drain Diode Forward Voltage

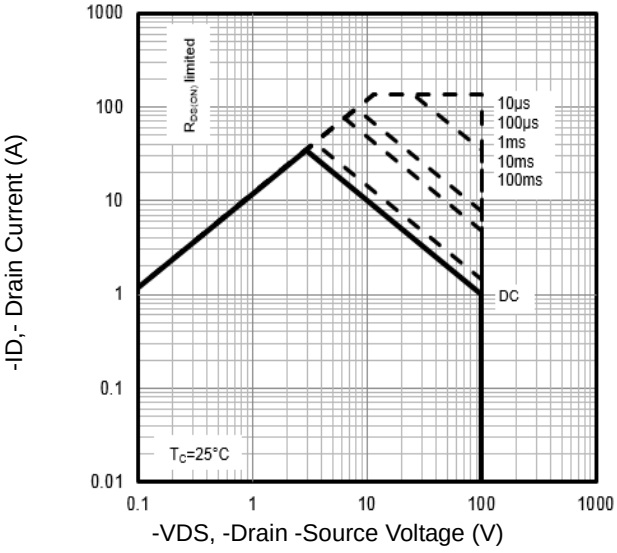


Fig6. Maximum Safe Operating Area

Typical Characteristics

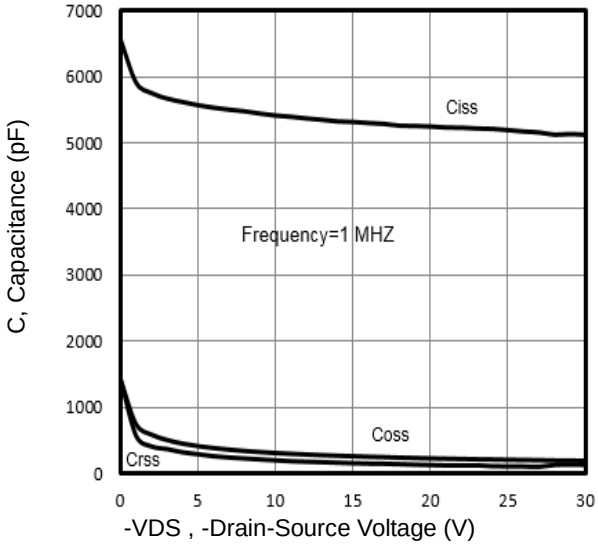


Fig7. Typical Capacitance Vs.Drain-Source Voltage

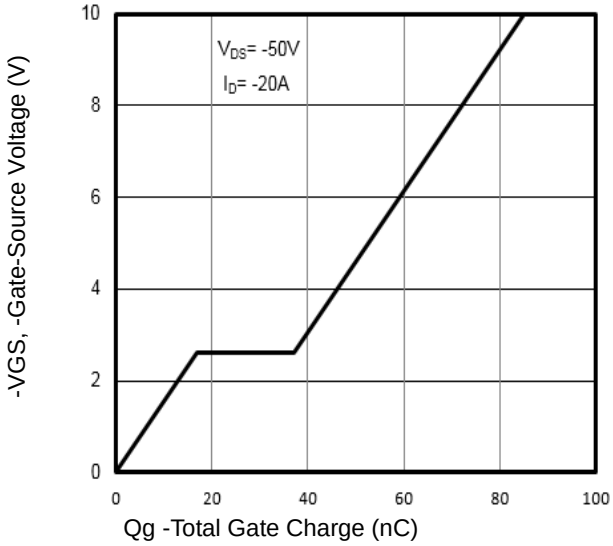


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

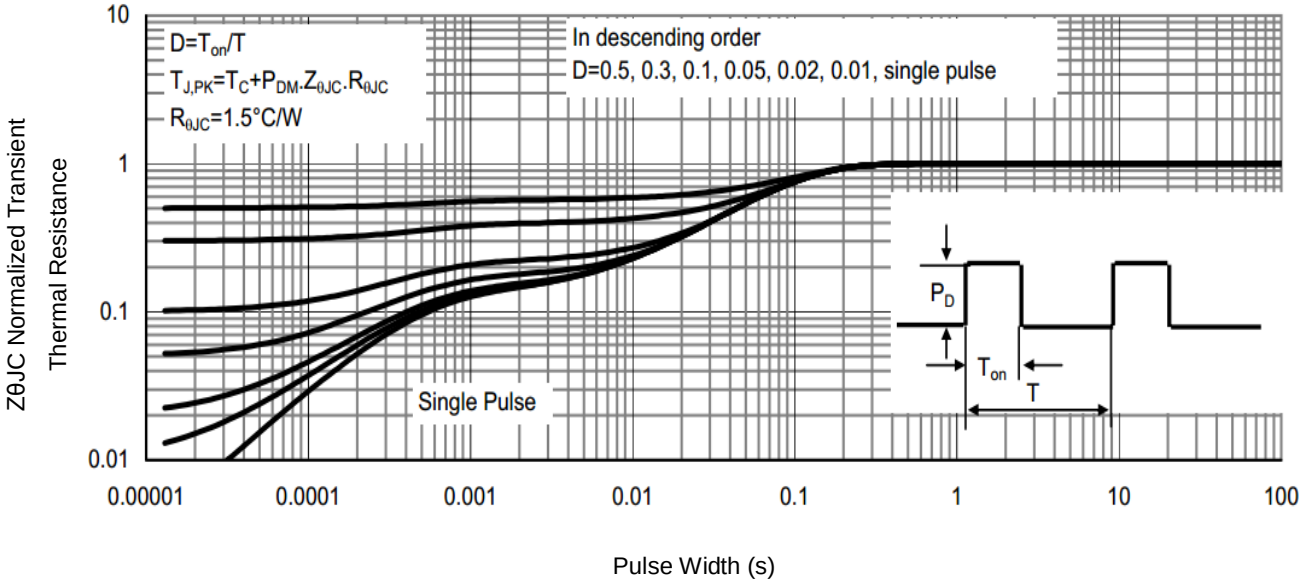


Fig9. Normalized Maximum Transient Thermal Impedance

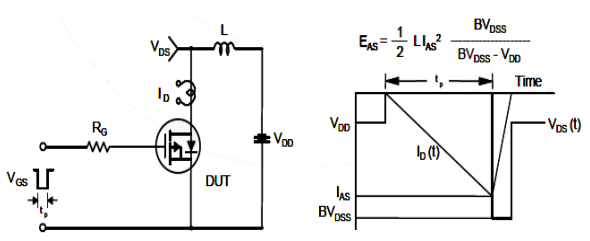


Fig10. Unclamped Inductive Test Circuit and Waveforms

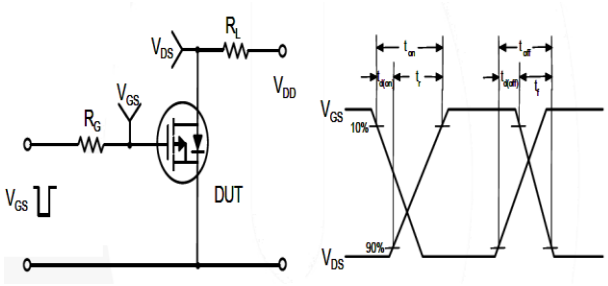
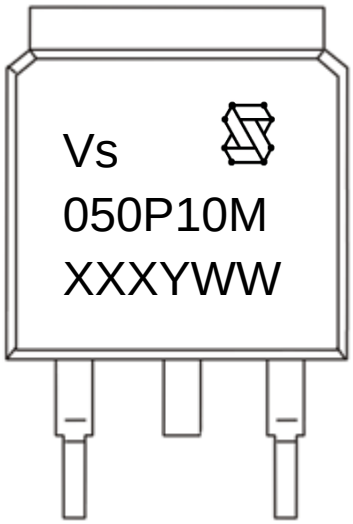


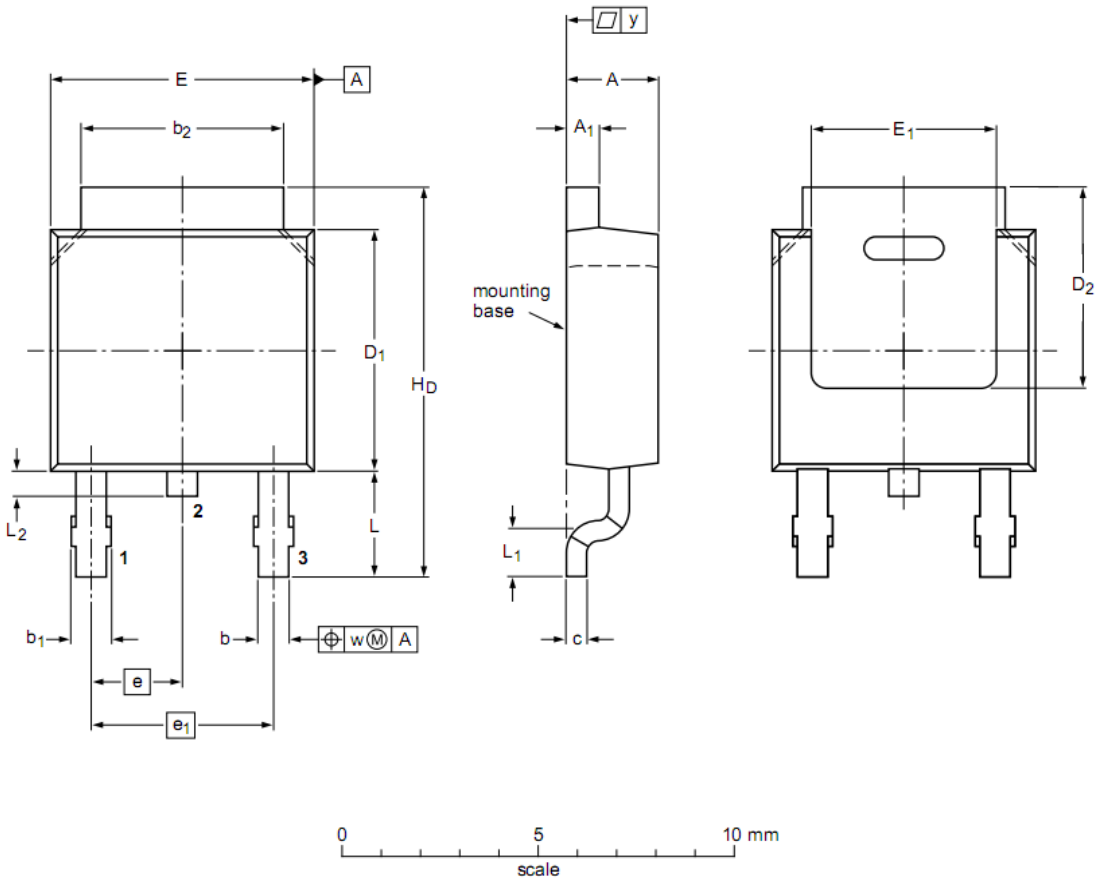
Fig11. Switching Time Test Circuit and waveforms

Marking Information



1st line： Vanguard Code（Vs）， Vanguard Logo
2nd line： Part Number（050P10M）
3rd line： Date code （XXXYWW）
XXX： Wafer Lot Number
Y： Year Code， e.g. E means 2017
WW： Week Code

TO-252 Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	2.20	2.30	2.38
A_1	0.46	0.50	0.63
b	0.64	0.76	0.89
b_1	0.77	0.85	1.14
b_2	5.00	5.33	5.46
c	0.458	0.508	0.558
D_1	5.98	6.10	6.223
D_2	5.21	--	--
E	6.40	6.60	6.731
E_1	4.40	--	--
e	2.286 BSC		
e_1	--	4.57	--
H_D	9.40	10.00	10.40
L	2.743 REF		
L_1	1.40	1.52	1.77
L_2	0.50	0.80	1.01
w	--	0.20	--
y	--	--	0.20

Notes:

1. Refer to JEDEC TO-252 variation AA
2. Dimension "E" does NOT include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.1524mm per side.
3. Dimension "D1" does NOT include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.1524mm per end.

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